Rochester Electronics

Datasheet

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
    - Class Q Military
    - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

National Semiconductor

LM760
High Speed Differential Comparator

General Description

The LM760 is a differential voltage comparator offering considerable speed improvement over the LM710 family and operates from symmetric supplies of ±4.5V to ±6.5V. The LM760 can be used in high speed analog-to-digital conversion systems and as a zero crossing detector in disc file and tape amplifiers. The LM760 output features balanced rise and fall times for minimum skew and close matching between the complementary outputs. The outputs are TTL compatible with a minimum sink capability of two gate loads.

Features

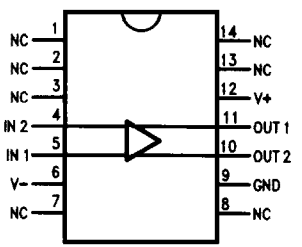
- Guaranteed high speed— 25 ns response time
- Guaranteed delay matching on both outputs
- Complementary TTL compatible outputs
- High sensitivity
- Standard supply voltages

Applications

- High speed A-to-D
- Peak or zero detector

Connection Diagrams

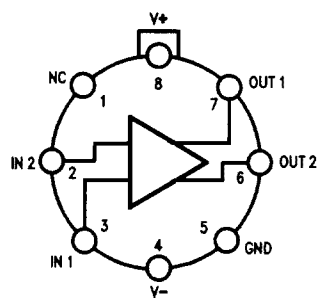
14-Lead DIP



TL/H/10067-2

Top View

8-Lead Metal Package

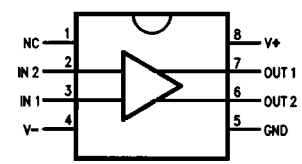


Lead 4 connected to case

TL/H/10067-1

Top View

8-Lead DIP



TL/H/10067-3

Top View

Ordering Information

Temperature Range		Package Type	NSC Package Drawing
Military −55°C to +125°C	**Commercial 0°C to +70°C**		
LM760J-14	LM760CJ-14	14-lead Ceramic DIP	J14A
LM760J	LM760CJ	8-lead Ceramic DIP	J08A
LM760H	LM760CH	8-lead Metal Can	H08A
	LM760CN	8-lead Plastic DIP	N08E

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature Range
- Metal Can and Ceramic DIP: −65°C to +175°C
- Molded DIP: −65°C to +150°C

Operating Temperature Range
- Military (LM760): −55°C to +125°C
- Commercial (LM760C): 0°C to +70°C

Lead Temperature
- Metal Can and Ceramic DIP (Soldering, 60 sec.): 300°C
- Molded DIP (Soldering, 10 sec.): 265°C

Internal Power Dissipation (Notes 1, 2)
- 8L-Metal Can: 1.00W
- 14L-Ceramic DIP: 1.36W
- 8L-Ceramic DIP: 1.30W

Positive Supply Voltage: +8.0V

Negative Supply Voltage: −8.0V

Peak Output Current: 10 mA

Differential Input Voltage: ±5.0V

Input Voltage: $V^+ \geq V_I \geq V^-$

ESD Susceptibility: TBD

LM760
Electrical Characteristics

$V_{CC} = \pm 4.5V$ to $\pm 6.5V$, $T_A = -55°C$ to $+125°C$, $T_A = 25°C$ for typical figures, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IO}	Input Offset Voltage	$R_S \leq 200\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current			0.5	7.5	μA
I_{IB}	Input Bias Current			8.0	60	μA
R_O	Output Resistance (Either Output)	$V_O = V_{OH}$		100		Ω
t_{PD}	Response Time	$T_A = 25°C$ (Note 3)		18	30	ns
		$T_A = 25°C$ (Note 4)			25	
		(Note 5)		16		
Δt_{PD}	Response Time Difference between Outputs (Note 1) (t_{PD} of $+V_{I1}$) − (t_{PD} of $-V_{I2}$)	$T_A = 25°C$			5.0	ns
	(t_{PD} of $+V_{I2}$) − (t_{PD} of $-V_{I1}$)	$T_A = 25°C$			5.0	
	(t_{PD} of $+V_{I1}$) − (t_{PD} of $+V_{I2}$)	$T_A = 25°C$			7.5	
	(t_{PD} of $-V_{I1}$) − (t_{PD} of $-V_{I2}$)	$T_A = 25°C$			7.5	
R_I	Input Resistance	f = 1.0 MHz		12		kΩ
C_I	Input Capacitance	f = 1.0 MHz		8.0		pF
$\Delta V_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Voltage	$R_S = 50\Omega$, $T_A = -55°C$ to $+125°C$		3.0		μV/°C
$\Delta I_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Current	$T_A = +25°C$ to $+125°C$		2.0		nA/°C
		$T_A = +25°C$ to $-55°C$		7.0		
V_{IR}	Input Voltage Range	$V_{CC} = \pm 6.5V$	±4.0	±4.5		V
V_{IDR}	Differential Input Voltage Range			±5.0		V
V_{OH}	Output Voltage HIGH (Either Output)	0 mA ≤ I_{OH} ≤ 5.0 mA, $V_{CC} = +5.0V$	2.4	3.2		V
		$I_{OH} = 80\ \mu A$, $V_{CC} = \pm 4.5V$	2.4	3.0		
V_{OL}	Output Voltage LOW (Either Output)	$I_{OL} = 3.2$ mA		0.25	0.4	V
I^+	Positive Supply Current	$V_{CC} = \pm 6.5V$		18	32	mA
I^-	Negative Supply Current	$V_{CC} = \pm 6.5V$		9.0	16	mA

LM760C
Electrical Characteristics

V_{CC} = ±4.5V to ±6.5V, T_A = 0°C to +70°C, T_A = 25°C for typical figures, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IO}	Input Offset Voltage	$R_S \leq 200\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current			0.5	7.5	μA
I_{IB}	Input Bias Current			8.0	60	μA
R_O	Output Resistance (Either Output)	$V_O = V_{OH}$		100		Ω
t_{PD}	Response Time	T_A = 25°C (Note 3)		18	30	ns
		T_A = 25°C (Note 4)			25	
		(Note 5)		16		
Δt_{PD}	Response Time Difference between Outputs (Note 1) (t_{PD} of $+V_{I1}$) − (t_{PD} of $-V_{I2}$)	T_A = 25°C			5.0	ns
	(t_{PD} of $+V_{I2}$) − (t_{PD} of $-V_{I1}$)	T_A = 25°C			5.0	
	(t_{PD} of $+V_{I1}$) − (t_{PD} of $+V_{I2}$)	T_A = 25°C			10	
	(t_{PD} of $-V_{I1}$) − (t_{PD} of $-V_{I2}$)	T_A = 25°C			10	
R_I	Input Resistance	f = 1.0 MHz		12		kΩ
C_I	Input Capacitance	f = 1.0 MHz		8.0		pF
$\Delta V_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Voltage	R_S = 50Ω, T_A = 0°C to +70°C		3.0		μV/°C
$\Delta I_{IO}/\Delta T$	Average Temperature Coefficient of Input Offset Current	T_A = +25°C to +70°C		5.0		nA/°C
		T_A = +25°C to 0°C		10		
V_{IR}	Input Voltage Range	V_{CC} = ±6.5V	±4.0	±4.5		V
V_{IDR}	Differential Input Voltage Range			±5.0		V
V_{OH}	Output Voltage HIGH (Either Output)	0 mA ≤ I_{OH} ≤ 5.0 mA, V_{CC} = +5.0V	2.4	3.2		V
		I_{OH} = 80 μA, V_{CC} = ±4.5V	2.5	3.0		
V_{OL}	Output Voltage LOW (Either Output)	I_{OL} = 3.2 mA		0.25	0.4	V
I^+	Positive Supply Current	V_{CC} = ±6.5V		18	34	mA
I^-	Negative Supply Current	V_{CC} = ±6.5V		9.0	16	mA

Note 1: $T_{J\,Max}$ = 175°C.

Note 2: Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 8L-Metal Can at 6.7 mW/°C, the 14L-Ceramic DIP at 9.1 mW/°C, and the 8L-Ceramic DIP at 8.7 mW/°C.

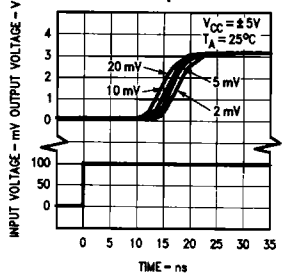
Note 3: Response time measured from the 50% point of a 30 mV_{p-p} 10 MHz sinusoidal input to the 50% point of the output.

Note 4: Response time measured from the 50% point of a 2.0 V_{p-p} 10 MHz sinusoidal input to the 50% point of the output.

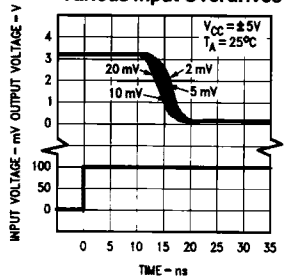
Note 5: Response time measured from the start of a 100 mV input step with 5.0 mV overdrive to the time when the output crosses the logic threshold.

Typical Performance Characteristics

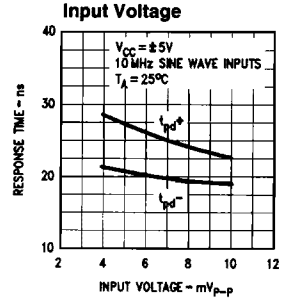
Response Time for Various Output Overdrives



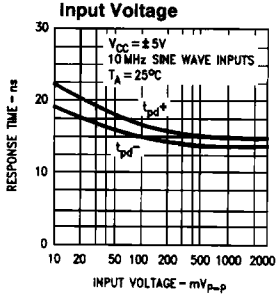
Response Time for Various Input Overdrives



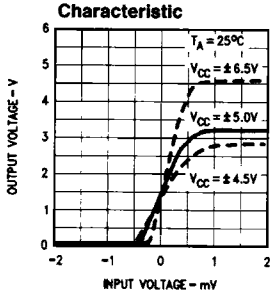
Response Time vs Input Voltage



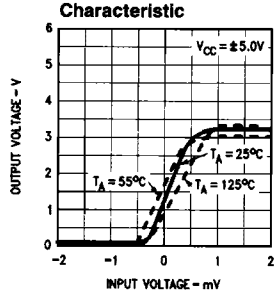
Response Time vs Input Voltage



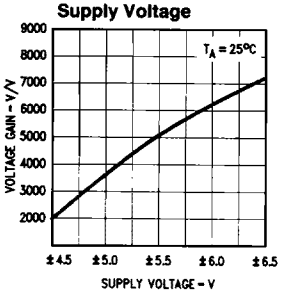
Voltage Transfer Characteristic



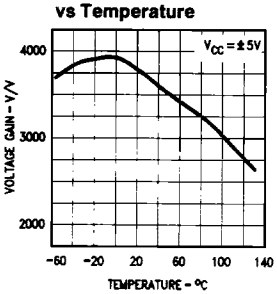
Voltage Transfer Characteristic



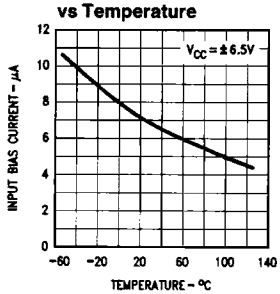
Voltage Gain vs Supply Voltage



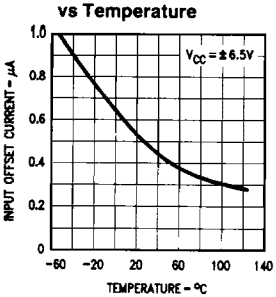
Voltage Gain vs Temperature



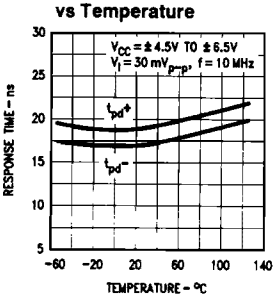
Input Bias Current vs Temperature



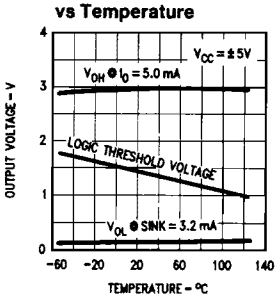
Input Offset Current vs Temperature



Response Time vs Temperature



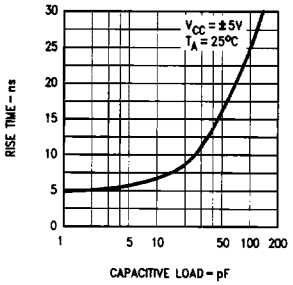
Output Voltage Levels vs Temperature



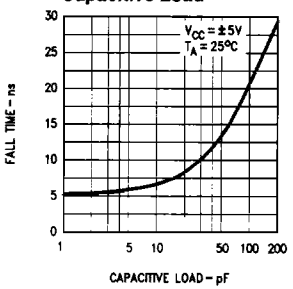
TL/H/10067–5

Typical Performance Characteristics (Continued)

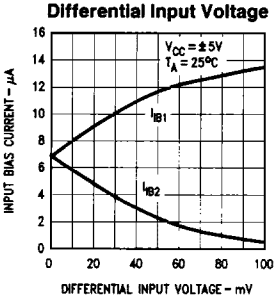
Rise Time vs Capacitive Load



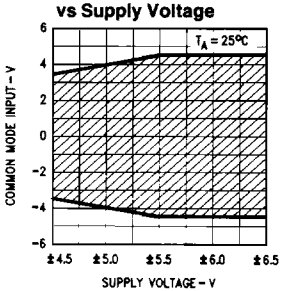
Fall Time vs Capacitive Load



Input Bias Current vs Differential Input Voltage



Common Mode Range vs Supply Voltage



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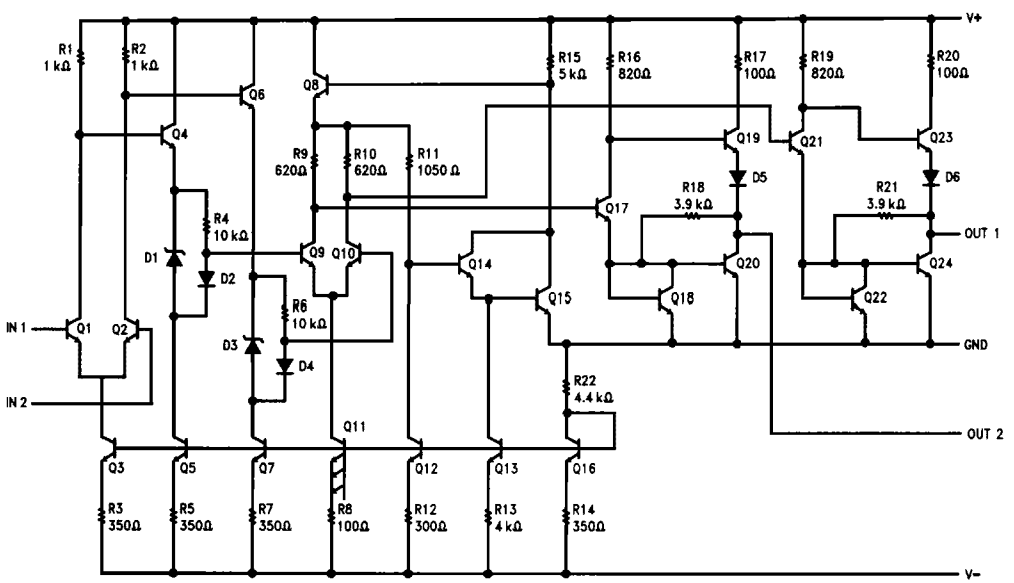
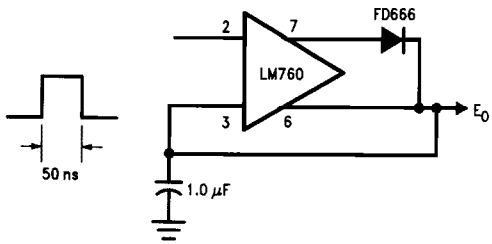
Equivalent Circuit



TL/H/10067–4

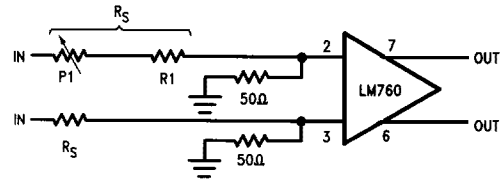
Typical Applications (Note 1)

Fast Positive Peak Detector



TL/H/10067-7

Line Receiver with High Common Mode Range



TL/H/10067-10

Common mode range = $\pm 4 \times \frac{R_S}{50}$ V

Differential Input Sensitivity = $5 \times \frac{R_S}{50}$ mV

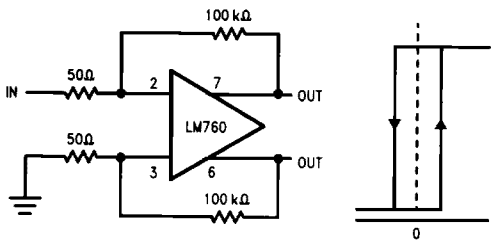
P_1 must be adjusted for optimum common mode rejection.

For R_S = 200Ω:

Common mode range = ±16V

Sensitivity = 20 mV

Level Detector with Hysteresis



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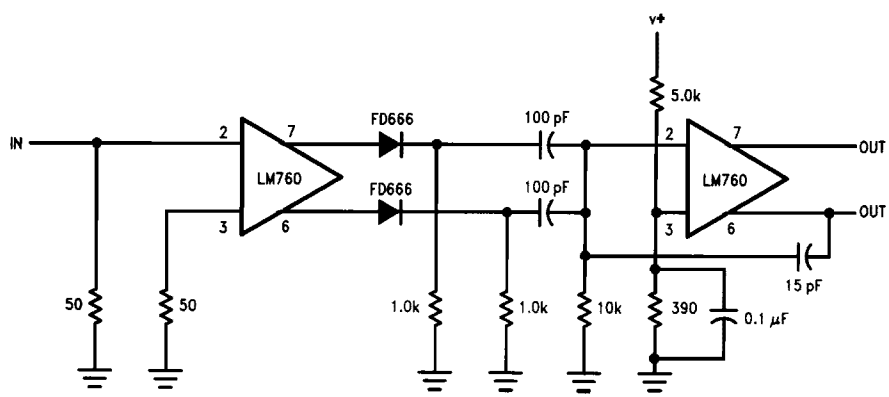
Zero Crossing Detector (Note 2)



TL/H/10067-9

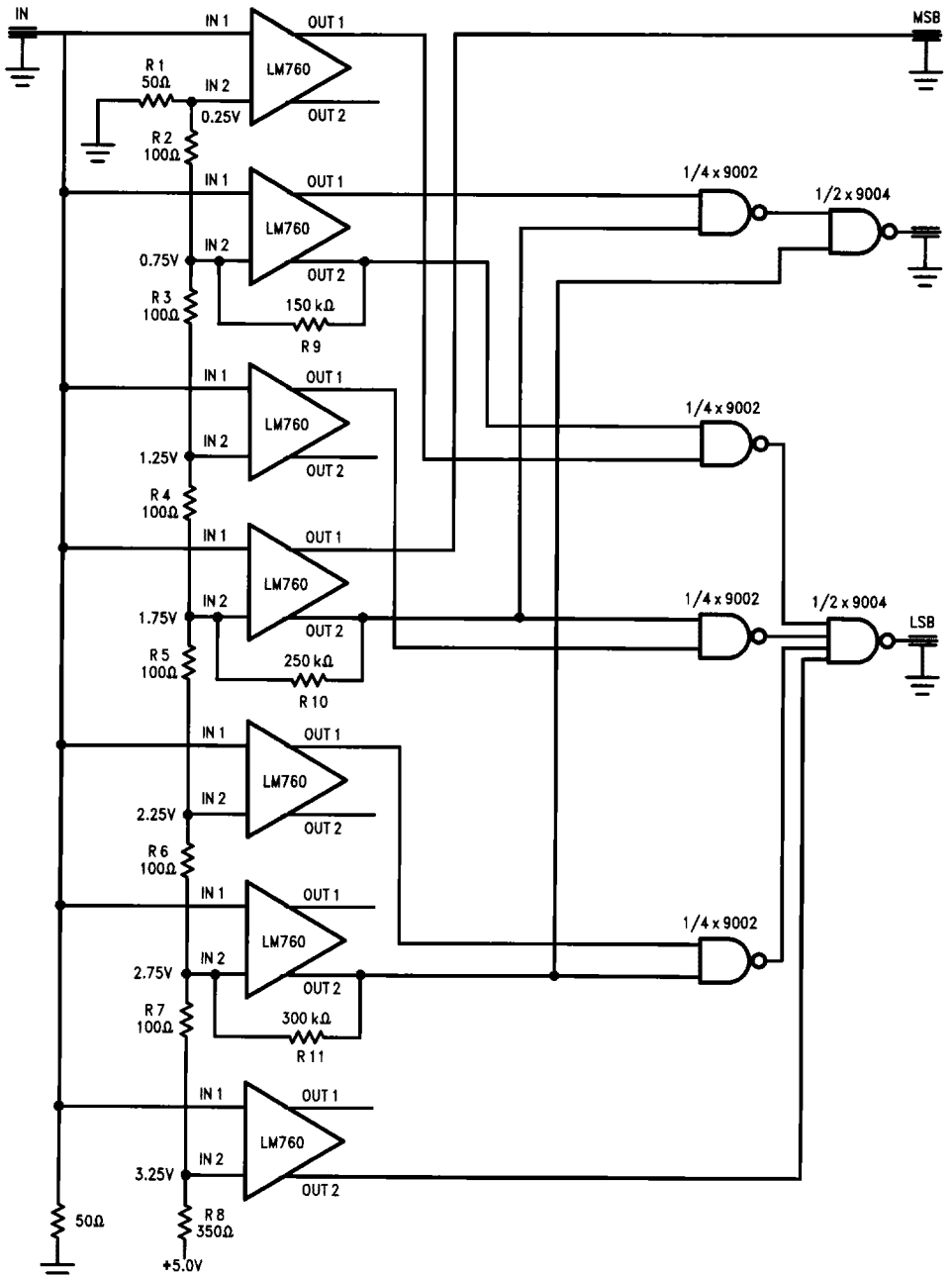
Total delay = 30 ns
Input Frequency = 300 Hz to 3.0 MHz
Minimum input voltage = 20 mV_{P-P}

Note 1: Lead numbers shown are for Metal Package only.

Note 2: All resistor values in ohms.

Typical Applications (Note 1) (Continued)

High Speed 3-Bit A/D Converter



TL/H/10067–11

Input voltage range = 3.5V
Typical conversion speed = 30 ns